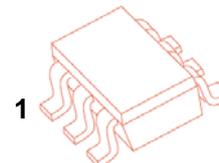
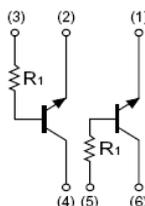


## dual digital transistors (NPN+NPN)

**SOT-363**

**FEATURES**

Two DTC144T chips in a package.

**Marking: H14**
**Equivalent circuit**

**Absolute maximum ratings (Ta=25°C)**

Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-base Voltage	50	V
$V_{CEO}$	Collector-emitter Voltage	50	V
$V_{EBO}$	Emitter-base Voltage	5	V
$I_C$	Collector current	100	mA
$P_D$	Power dissipation	150	mW
$T_J$	Junction temperature	150	°C
$T_{stg}$	Storage temperature	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50\mu A, I_E=0$	50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50\mu A, I_C=0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=50V, I_E=0$			500	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=4V, I_C=0$			500	nA
DC current transfer ration	$h_{FE}$	$V_{CE}=5V, I_C=1mA$	100		600	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=5mA, I_B=0.5mA$			0.3	V
Transition frequency	$f_T$	$V_{CE}=10V, I_C=5mA, f=100MHz$		250		MHz
Input resistance	$R_1$		32.9		61.1	KΩ